Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN0606-3 (SOT8001) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Leadless ultra small and ultra thin SMD plastic package: 0.62 x 0.62 x 0.37 mm

3. Applications

- · Relay driver
- High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	٧
V _{GS}	gate-source voltage			-10	-	10	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-520	mA
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -410 \text{ mA}; T_j = 25 \text{ °C}$		-	1.3	1.6	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source		
3	D	drain	Transparent top view DFN0606-3 (SOT8001)	G S S 017aaa259

6. Ordering information

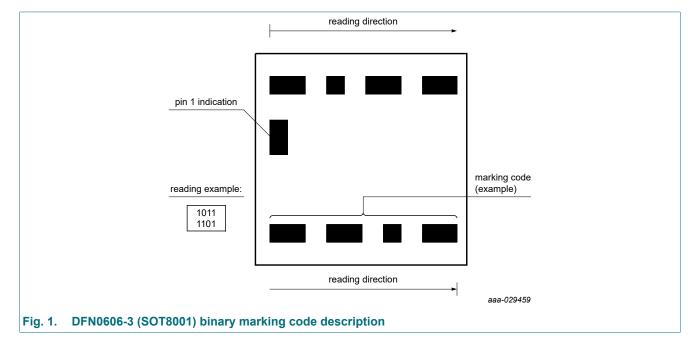
Table 3. Ordering information

Type number					
	Name	Description	Version		
PMH1200UPE		plastic, leadless ultra small package; 3 terminals; body 0.62 x 0.62 x 0.37 mm	SOT8001		

7. Marking

Table 4. Marking codes

Type number	Marking code
PMH1200UPE	0001 0101



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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage			-10	10	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-520	mA
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-330	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-2	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	380	mW
			[1]	-	710	mW
		T _{sp} = 25 °C		-	2.8	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode			1		'
Is	source current	T _{amb} = 25 °C	[1]	-	-540	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

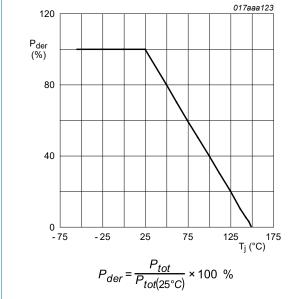


Fig. 2. Normalized total power dissipation as a function of junction temperature

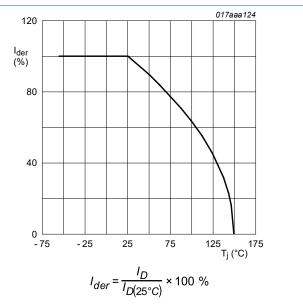


Fig. 3. Normalized continuous drain current as a function of junction temperature

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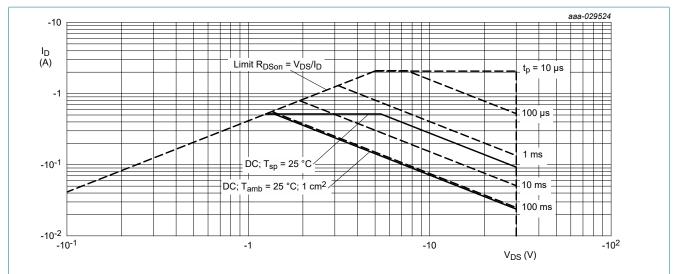


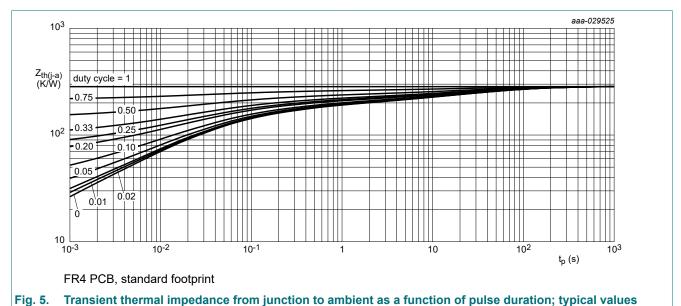
Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

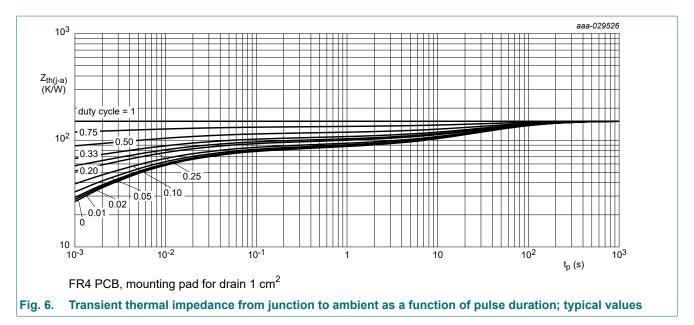
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from	in free air	[1]	-	285	330	K/W	
	junction to ambient		[2]	-	150	175	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	40	45	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μA
		V _{GS} = 2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -410 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	1.3	1.6	Ω
	resistance	V _{GS} = -4.5 V; I _D = -410 mA; T _j = 150 °C	-	2.2	2.4	Ω
		V_{GS} = -2.5 V; I_D = -320 mA; T_j = 25 °C	-	1.8	2.7	Ω
		V_{GS} = -1.8 V; I_D = -80 mA; T_j = 25 °C	-	2.4	4.7	Ω
		$V_{GS} = -1.5 \text{ V}; I_D = -10 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	3	7.1	Ω
9 _{fs}	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -520 \text{ mA}; T_j = 25 \text{ °C}$	-	670	-	mS
R_G	gate resistance	f = 1 MHz	-	24	-	Ω
Dynamic ch	naracteristics			·	·	
Q _{G(tot)}	total gate charge	$V_{DS} = -15 \text{ V}; I_D = -400 \text{ mA}; V_{GS} = -5 \text{ V};$	-	0.4	1	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	$V_{DS} = -15 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	33	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	5.5	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = -15 \text{ V}; I_D = -400 \text{ mA}; V_{GS} = -5 \text{ V};$	-	1	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	2	-	ns
t _{d(off)}	turn-off delay time		-	4	-	ns
t _f	fall time		-	3	-	ns
Source-dra	in diode		'			
V_{SD}	source-drain voltage	$I_S = -540 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = 25 ^{\circ}\text{C}$	-	-1	-1.2	V

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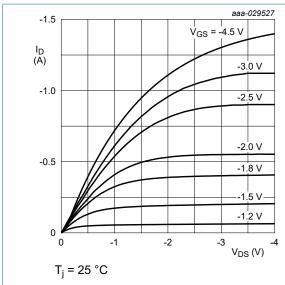


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

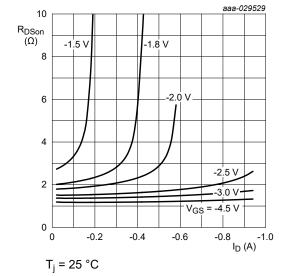


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

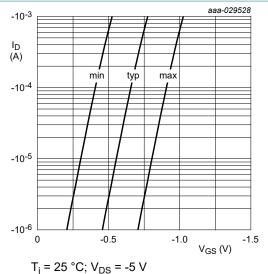


Fig. 8. Sub-threshold drain current as a function of

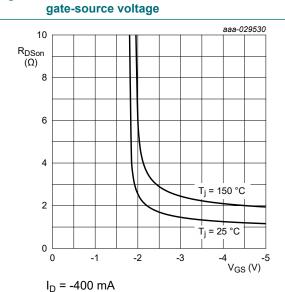


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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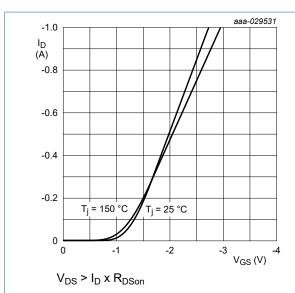


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

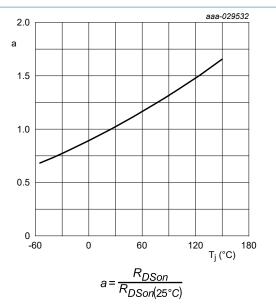


Fig. 12. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

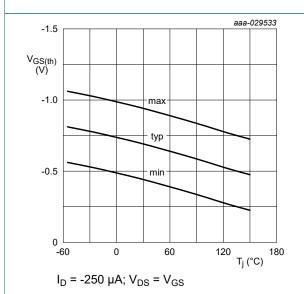
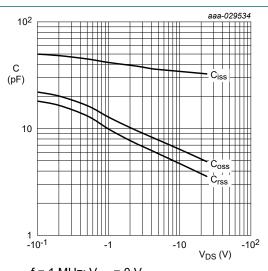


Fig. 13. Gate-source threshold voltage as a function of junction temperature



f = 1 MHz; V_{GS} = 0 V

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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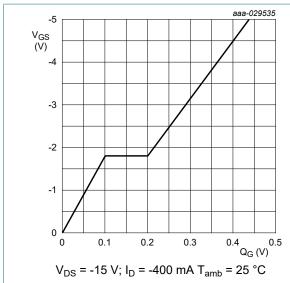


Fig. 15. Gate-source voltage as a function of gate charge; typical values

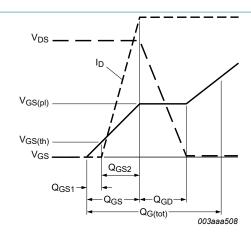


Fig. 16. Gate charge waveform definitions

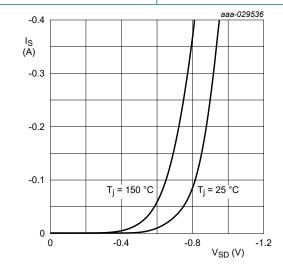
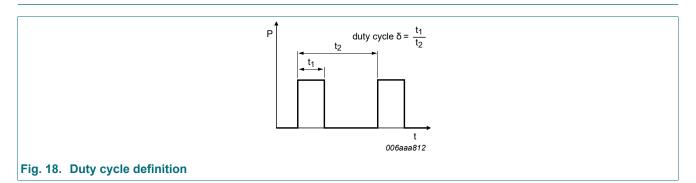


Fig. 17. Source current as a function of source-drain voltage; typical values

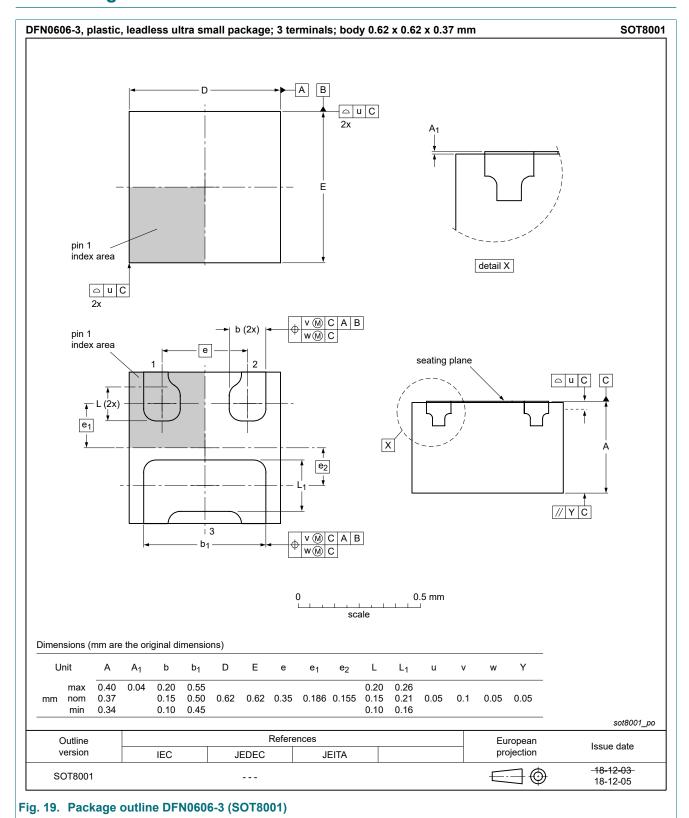
11. Test information

 $V_{GS} = 0 V$



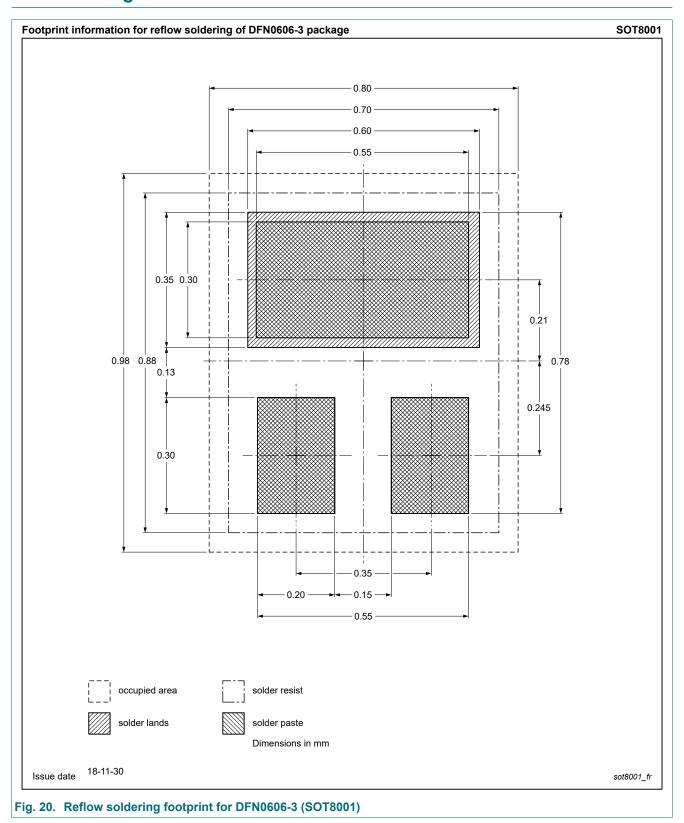
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMH1200UPE v.1	20190304	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PMH1200UPE

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Date of release: 4 March 2019

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